

INFORMATION DISCLOSURE STATEMENT BY APPLICANT Form PTO-1449 (Modified) (Use several sheets if necessary)				COMPLETE IF KNOWN	
				Application Number	10/782,564
				Confirmation Number	
				Filing Date	02/18/04
				First Named Inventor	Jack Zezhong Peng
				Group Art Unit	2827
Examiner Name	Huan Hoang				
Sheet	1	of	4	Attorney Docket No.	384848013US1

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.	U.S. Patent or Application		Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		NUMBER	Kind Code (if known)			
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WJH		JP	61292295		Fujitsu Ltd.	12/23/86		

OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume issue number(s), publisher, city and/or country where published.	T
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<i>HH</i>		DeGRAAF, C., et al, A Novel High-Density Low-Cost Diode Programmable Read Only Memory, IEEE, 1996.	

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